## HITANO HITANO ENTERPRISE CORP. <br> 「ENTERPRISE CORP.@

## S1A THRU S1M

## TECHNICAL SPECIFICATIONS <br> OF SURFACE MOUNT SILICON RECTIFIER

## VOLTAGE RANGE - 50 to 1000 Volts

## FEATURES

* Ideal for surface mounted applications
* Low leakage current
* Glass passivated junction


## MECHANICAL DATA

* Case: Molded plastic
* Epoxy: UL 94V-0 rate flame retardant
*Terminals: Solder plated, solderable per
MIL-STD-750, Method 2026
* Polarity: As marked
* Mounting position: Any
* Weight: 0.093 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS
Ratings at $25^{\circ} \mathrm{C}$ ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz , resistive or inductive
load.
For capacitive load, derate current by $20 \%$.

CURRENT - 1.0 Ampere



|  | SYMBOL | S1A | S1B | S1D | S1G | S1J | S1K | S1M | UNITS |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Maximum Recurrent Peak Reverse Voltage | VRrm | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | Volts |
| Maximum RMS Voltage | VRms | 35 | 70 | 140 | 280 | 420 | 560 | 700 | Volts |
| Maximum DC Blocking Voltage | VDC | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | Volts |
| Maximum Average Forward Rectified Current at $\mathrm{TA}=75^{\circ} \mathrm{C}$ | 10 | 1.0 |  |  |  |  |  |  | Amps |
| Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method) | IFSM | 30 |  |  |  |  |  |  | Amps |
| Maximum Instantaneous Forward Voltage at 1.0A DC | VF | 1.1 |  |  |  |  |  |  | Volts |
| Maximum DC Reverse Current $@^{\text {a }}$ A $=25^{\circ} \mathrm{C}$ | IR | 5.0 |  |  |  |  |  |  | uAmps |
| at Rated DC Blocking Voltage $\quad @$a |  | 100 |  |  |  |  |  |  |  |
| Maximum Reverse Recovery Time (Note 3) | trr | 2.5 |  |  |  |  |  |  | uSec |
| Typical Thermaesistance (Note 2) | R $\theta \mathrm{JL}$ | 12 |  |  |  |  |  |  | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Typical Junction Capacitance (Note 1) | CJ | 30 |  |  |  |  |  |  | pF |
| Operating and Storage Temperature Range | TJ,Tstg | -65 to +175 |  |  |  |  |  |  | ${ }^{0} \mathrm{C}$ |

NOTES : 1. Measured at 1 MHz and applied reverse voltage of 4.0 volts.
2. Thermal Resistance (Junction to Ambient), $0.2 \times 0.2 \mathrm{in}^{2}\left(5 \times 5 \mathrm{~mm}^{2}\right)$ copper pads to each terminal.
3. Test Conditions: $\mathrm{IF}=0.5 \mathrm{~A}, \mathrm{IR}=1.0 \mathrm{~A}, \mathrm{IRR}=0.25 \mathrm{~A}$.

FIG. 1-TYPICAL FORWARD CURRENT DERATING CURVE


FIG. 3 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS


FIG. 2 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT


FIG. 4 - TYPICAL REVERSE CHARACTERISTICS


FIG. 5 - TYPICAL JUNCTION CAPACITANCE


